What is claimed is:

1. A method comprising:

a) providing a doped semiconductor wafer comprising a front side, a back side, and a pn junction;

b) selectively applying a resist composition on top of the front side of the semiconductor wafer, the resist composition comprises one or more hydrogenated rosin resins, the hydrogenated rosin resins are solids at room temperature, one or more hydrogenated rosin resin esters, the hydrogenated rosin resin esters are liquids at room temperature, and one or more fatty acids; and

c) applying an etch composition to the semiconductor to etch away exposed sections of the front side of the semiconductor to form current tracks.

2. The method of claim 1, wherein the front side of the semiconductor further comprises an antireflective layer.

3. The method of claim 1, wherein the hydrogenated rosin resin is derived from abietic acid or pimaric acid.

4. The method of claim 1, wherein the hydrogenated rosin resin ester is derived from abietic acid or pimaric acid.

5. The method of claim 1, wherein a weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2:1 to 4:1.

6. The method of claim 1, wherein an emitter layer of the front side of the semiconductor wafer is n++ doped.

7. The method of claim 1, wherein the semiconductor wafer is a mono cast wafer, monocrystalline wafer or a polycrystalline wafer.

8. A composition comprising one or more hydrogenated rosin resins, one or more hydrogenated rosin resin esters, and one or more fatty acids, the one or more hydrogenated rosin resins are solids at room temperature and the one or more hydrogenated rosin resin esters are liquids at room temperature, the weight ratio of the one or more hydrogenated rosin resins to the one or

more hydrogenated rosin resin esters is 2:1 to 4:1.

9. The composition of claim 8, wherein the weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2.3:1 to 3.8:1.

10. The composition of claim 9, wherein the weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2.5:1 to 3.3:1.

What is claimed is:

1. A method comprising:

a) providing a doped semiconductor wafer comprising a front side, a back side, and a pn junction;

b) selectively applying a resist composition on top of the front side of the semiconductor wafer, the resist composition comprises one or more hydrogenated rosin resins, the hydrogenated rosin resins are solids at room temperature, one or more hydrogenated rosin resin esters, the hydrogenated rosin resin esters are liquids at room temperature, a weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2:1 to 4:1, and one or more fatty acids; and

c) applying an etch composition to the semiconductor to etch away exposed sections of the front side of the semiconductor to form current tracks.

2. The method of claim 1, wherein the front side of the semiconductor further comprises an antireflective layer.

3. The method of claim 1, wherein the hydrogenated rosin resin is derived from abietic acid or pimaric acid.

4. The method of claim 1, wherein the hydrogenated rosin resin ester is derived from abietic acid or pimaric acid.

5. The method of claim 1, wherein an emitter layer of the front side of the semiconductor wafer is n++ doped.

6. The method of claim 1, wherein the semiconductor wafer is a mono cast wafer, monocrystalline wafer or a polycrystalline wafer.

7. A composition comprising one or more hydrogenated rosin resins, one or more hydrogenated rosin resin esters, and one or more fatty acids, the one or more hydrogenated rosin resins are solids at room temperature and the one or more hydrogenated rosin resin esters are liquids at room temperature, the weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2:1 to 4:1.

8. The composition of claim 7, wherein the weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2.3:1 to 3.8:1.

9. The composition of claim 8, wherein the weight ratio of the one or more hydrogenated rosin resins to the one or more hydrogenated rosin resin esters is 2.5:1 to 3.3:1.